What Is Claimed Is:

1. A liquid crystal display device, comprising:

a substrate;

an organic insulating film formed on the substrate;

an alignment film having a first etch rate formed on the organic insulating film; and

a silicon nitride layer having a second etch rate formed between the alignment film and the organic insulating film,

wherein the first etch rate is different from the second etch rate.

2. The device according to claim 1, wherein the alignment film is eliminated by dry-etching during rework processing.

3. The device according to claim 2, wherein the dry-etching is carried out by using at least one compound gas of SF_6, O_2, O_2+Cl_2, and CF_4.

4. The device according to claim 3, wherein a ratio of the compound gas is at least about SF_6:O_2=1:50.

5. The device according to claim 3, wherein a ratio of the compound gas is at least about SF_6:O_2=1:70.

6. The device according to claim 3, wherein the dry-etching usess a radio frequency power of about 500-1500W.

7. The liquid crystal display device according to claim 1, wherein the silicon nitride layer includes hydrogen.

8. The device according to claim 1, further comprising:

a gate line on the substrate;

a data line crossing the gate line;

a gate electrode connected to the gate line;

a gate insulating film covering the gate electrode and the gate line;

a semiconductor layer formed on the gate insulating film;

a source electrode connected to the data line; and

a drain electrode formed away from the source electrode with a channel of a fixed size formed therebetween.

9. The device according to claim 8, wherein a pixel electrode electrically contacts the drain electrode and overlaps at least one of the data line and the gate line.

10. A method of fabricating a liquid crystal display device, comprising the steps of:

forming an organic insulating film on a substrate;

forming an alignment film having a first etch rate on the organic insulating film; and

forming a silicon nitride layer having a second etch rate between the alignment film and the organic insulating film,

wherein the first etch rate is different from the second etch rate.

11. The method according to claim 10, further including eliminating the alignment film by dry-etching during rework processing.

12. The method according to claim 11, wherein the dry-etching is carried out by using at least one compound gas of SF_6, O_2, O_2+Cl_2, and CF_4.

13. The method according to claim 12, wherein a ratio of the compound gas is at least about SF_6:O_2=1:50.

14. The method according to claim 12, wherein a ratio of the compound gas is at least about $SF_6:O_2=1:70$.

15. The method according to claim 12, wherein the dry-etching uses a radio frequency power of about 500-1500W.

16. The method according to claim 10, wherein the silicon nitride layer includes hydrogen.

17. The method according to claim 10, further including the steps of:

forming a gate line and a gate electrode on the substrate;

forming a gate insulating film on the gate line, the gate electrode and the substrate;

forming a semiconductor layer on the gate insulating film; and

forming a data line, a source electrode and a drain electrode on the gate insulating film.

18. The method according to claim 17, further including the step of forming a pixel electrode on the silicon nitride layer to overlap at least one of the data line and the gate line.

19. A method of reworking an alignment film of a liquid crystal display device, comprising the steps of:

forming an organic protective film on a substrate;

forming a silicon nitride layer having a first etch rate on the organic protective film;

forming a first alignment film on the silicon nitride layer;

detecting at least one irregularity of the first alignment film formed on the silicon nitride layer;

eliminating the first alignment film with a second etch rate different from the first etch rate of the silicon nitride layer; and

forming a second alignment film on the silicon nitride layer.

20. The method of according to claim 19, wherein the step of eliminating the first alignment film includes dry-etching during rework processing.

21. The method according to claim 20, wherein the dry-etching is carried out by using at least one compound gas of SF_6, O_2, O_2+Cl_2, and CF_4.

22. The method according to claim 21, wherein a ratio of the compound gas is at least about SF_6:O_2=1:50.

23. The method according to claim 21, wherein a ratio of the compound gas is at least about $SF_6:O_2=1:70$.

24. The method according to claim 21, wherein the dry-etching includes a radio frequency power of about 500-1500W.

25. The method according to claim 19, wherein the silicon nitride layer includes hydrogen.

26. The method according to claim 19, further including the steps of:

forming a gate line and a gate electrode on the substrate;

forming a gate insulating film on the gate line, the gate electrode and the substrate;

forming a semiconductor layer on the gate insulating film; and

forming a data line, a source electrode and a drain electrode on the gate insulating film.

27. The method according to claim 26, further including the step of forming a pixel electrode on the silicon nitride layer to overlap at least one of the data line and the gate line.